

### 3.4µA, 90kHz, RRIO CMOS Operational Amplifiers

### **General Description**

The HTC8521 (single), HTC8522 (dual) and HTC8524 (quad) are ultra-low power operational amplifiers that provide 90kHz bandwidth with only 3.4µA quiescent current. These rail-to-rail input and output amplifiers are specifically designed for battery-powered applications. The input common-mode voltage range extends 300mV beyond the power-supply rails and the output swings to only 6mV of the rails, maintaining wide dynamic range. Unlike some micro-power op-amps, these parts are unity-gain stable. The HTC852x family features a low input bias current that allows the use of large source and feedback resistors.

The HTC852x op-amps are specified for single or dual power supplies of +2.3V to +5.5V. All models are specified over the extended industrial temperature range of −40°C to +125°C. The HTC8521 is available in 5-lead SC70 and SOT-23 packages. The HTC8522 is available in 8-lead MSOP and SOIC packages. The HTC8524 is available in 14-lead TSSOP and SOIC packages.

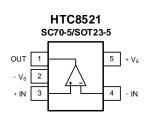
### **Features and Benefits**

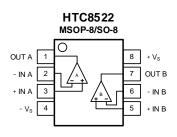
- Low Supply Current: 4.2 µA Maximum per Amplifier
- Gain-Bandwidth: 90 kHz
- Unity Gain Stable
- Low Offset Voltage: 3.0 mV Maximum
- Rail-to-Rail Input and Output
  - Input Range: 300 mV Beyond Rails
- DC Precision
  - CMRR: 102 dBPSRR: 102dB
  - A<sub>VOL</sub>: 110dB
- Output Swings to 6 mV of Rails
- Operating Power Supply: +2.3 to +5.5 V
- Operating Temperature Range: -40°C to +125°C

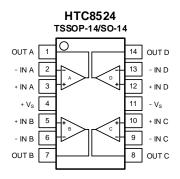
# **Applications**

- Battery-Powered Systems
- Sensor Interfaces, Remote Sensing
- Supply Current Sensing
- Safety Monitoring
- Portable Medical Instruments
- Analog Active Filters
- ASIC Input or Output Amplifier

### **Pin Configurations (Top View)**









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### **Pin Description**

Symbol	Description
-IN	Inverting Input of the Amplifier. The Voltage range can go from (V $_{\rm S-}-0.3\rm V)$ to (V $_{\rm S+}+0.3\rm V).$
+IN	Non-Inverting Input of Amplifier. This pin has the same voltage range as -IN.
+V <sub>S</sub>	Positive Power Supply. The voltage is from 2.3V to 5.5V. Split supplies are possible as long as the voltage between $V_{S^+}$ and $V_{S^-}$ is between 2.3V and 5.5V. A bypass capacitor of $0.1\mu F$ as close to the part as possible should be used between power supply pins or between supply pins and ground.
-V <sub>S</sub>	Negative Power Supply. It is normally tied to ground. It can also be tied to a voltage other than ground as long as the voltage between $V_{S+}$ and $V_{S-}$ is from 2.3V to 5.5V. If it is not connected to ground, bypass it with a capacitor of $0.1\mu F$ as close to the part as possible.
OUT	Amplifier Output.
N/C	No Connection.

## **Ordering Information**

Type Number	Package Name	Package Quantity	Marking Code
HTC8521XC5/R6	SC70-5	Tape and Reel, 3 000	C21
HTC8521XT5/R6	SOT23-5	Tape and Reel, 3 000	C21
HTC8522XV8/R6	MSOP-8	Tape and Reel, 3 000	C22X
HTC8522XS8/R8	SO-8	Tape and Reel, 4 000	C22X
HTC8524XT14/R6	TSSOP-14	Tape and Reel, 3 000	C24X
HTC8524XS14/R5	SO-14	Tape and Reel, 2 500	C24X

### **Limiting Value**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Absolute Maximum Rating
Supply Voltage, $V_{S+}$ to $V_{S-}$	7.0V
Common-Mode Input Voltage	$V_{S-} - 0.5V$ to $V_{S+} + 0.5V$
Storage Temperature Range	-65°C to +150°C(TJ)
Junction Temperature	160℃
Lead Temperature Range (Soldering 10 sec)	260℃
	HBM $\pm 4000$ V
Electrostatic Discharge Voltage	CDM $\pm 2000$ V
	MM $\pm 400$ V

**NOTE 1:** Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 2: Provided device does not exceed maximum junction temperature (TJ) at any time.





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### **Electrical Characteristics**

 $V_{\rm S}=5.0 V,~T_{\rm A}=+25\,{}^{\circ}\!\!{\rm C},~V_{\rm CM}=V_{\rm S}/2,~V_{\rm O}=V_{\rm S}/2,~{\rm and}~R_{\rm L}=10 {\rm k}\Omega$  connected to  $V_{\rm S}/2,~{\rm unless}$  otherwise noted. Boldface limits apply over the specified temperature range,  $T_{\rm A}=-40$  to +125  ${}^{\circ}\!\!{\rm C}.$ 

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
INPUT CI	HARACTERISTICS						
\/	Input offset voltage		-4.2	±0.5	+4.2	mV	
V <sub>os</sub>	over Temperature		-4.5		+4.5	IIIV	
V <sub>os</sub> TC	Offset voltage drift	over Temperature		2		μV/°C	
	Input bias current			1	20	n ^	
l <sub>B</sub>	over Temperature				800	— pA	
I <sub>os</sub>	Input offset current			1		pА	
$V_{CM}$	Common-mode voltage range		V <sub>S-</sub> -0.3		V <sub>S+</sub> +0.3	V	
	Common-mode rejection ratio	V <sub>CM</sub> = 0.05V to 3.5V	80	102			
CMRR	over Temperature		70			dB	
		$V_{CM} = V_{S_{-}} - 0.1 \text{ to } V_{S_{+}} + 0.1 \text{ V}$	72	88			
	over Temperature	V <sub>CM</sub> - V <sub>S-</sub> -0.1 (U V <sub>S+</sub> +0.1 V	60				
Δ	Open-loop voltage gain	$V_0 = 0.05$ to 3.5 V	90	110		dB	
$A_{VOL}$	over Temperature	v <sub>0</sub> – 0.03 to 3.3 v	82			uБ	
$R_{IN}$	Input resistance		100			GΩ	
C <sub>IN</sub> Input cap	Input capacitance	Differential		2.0		pF	
OIN Input capacitance		Common mode		3.5		Рі	
OUTPUT	CHARACTERISTICS						
$V_{OH}$	High output voltage swing			V <sub>S+</sub> -6		mV	
$V_{OL}$	Low output voltage swing			6 52		mV	
I <sub>sc</sub>	Short-circuit current	Source current through $10\Omega$				mA	
'SC	Short circuit current	Sink current through $10\Omega$		41		1117 (	
DYNAMIC	C PERFORMANCE						
GBW	Gain bandwidth product	f = 1kHz		90		kHz	
$\Phi_{M}$	Phase margin	$C_L = 100pF$		66		0	
SR	Slew rate	$G = +1$ , $C_L = 100pF$ , $V_O = 1.5V$ to 3.5V		0.04		V/µs	
t <sub>S</sub>	Settling time	To 0.1%, G = +1, 2V step		51		– µs	
'S	Settling time	To 0.01%, G = +1, 2V step		55		μσ	
NOISE P	ERFORMANCE						
$V_n$	Input voltage noise	f = 0.1 to 10 Hz		12		$\mu V_{\text{P-P}}$	
e <sub>n</sub>	Input voltage noise density	f = 10kHz		90		nV/√Hz	
POWER	SUPPLY						
$V_S$	Operating supply voltage		2.3		5.5	V	
PSRR	Power supply rejection ratio	$V_S = 2.7V \text{ to } 5.5V, V_{CM} < V_{S+} - 2V$	80	102		dB	
	over Temperature	3, .CM .2+	75				



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## **Electrical Characteristics** (continued)

 $V_S=5.0V,~T_A=+25\,{}^\circ\!\!C,~V_{CM}=V_S/2,~V_O=V_S/2,$  and  $R_L=10k\Omega$  connected to  $V_S/2,~unless$  otherwise noted. Boldface limits apply over the specified temperature range,  $T_A=-40$  to +125  ${}^\circ\!\!C.$ 

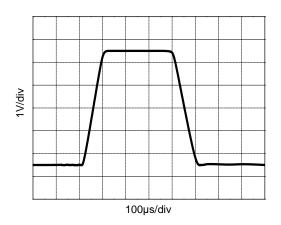
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I <sub>Q</sub>	Quiescent current (per amplifier)			3.4	4.2	μA
-	over Temperature				5	
THERMA	L CHARACTERISTICS					
T <sub>A</sub>	Specified temperature range		-40		+125	°C
		SC70-5		333		
		SOT23-5		190		
Δ	Package Thermal	MSOP-8		216		°C/W
$\theta_{JA}$	Resistance	SO-8		125		C/VV
		TSSOP-14		112		
		SO-14		115		



### 3.4µA, 90kHz, RRIO CMOS Operational Amplifiers

### **Typical Performance Characteristics**

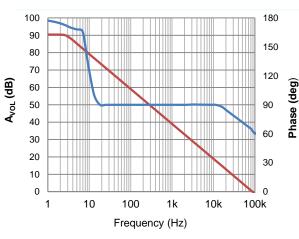
At  $T_A = +25$ °C,  $V_{CM} = V_S/2$ , and  $R_L = 10k\Omega$  connected to  $V_S/2$ , unless otherwise noted.

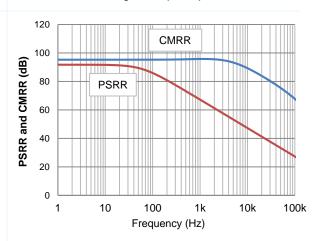


Nib/Vm03

Large Signal Step Response.

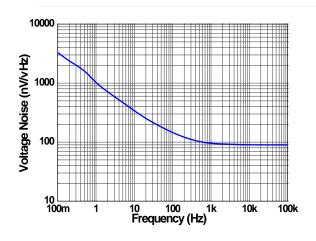
Small Signal Step Response.

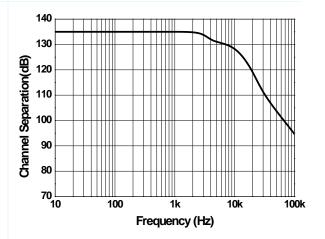




Open-loop Gain and Phase as a function of Frequency.

Power Supply and Common-mode Rejection Ratio as a function of Frequency.





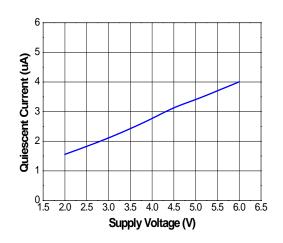
Input Voltage Noise Spectral Density as a function of Frequency.

Channel Separation as a function of Frequency.

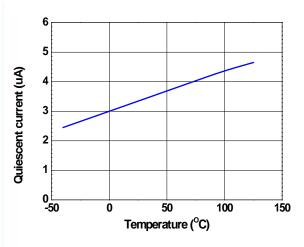


### **Typical Performance Characteristics** (continued)

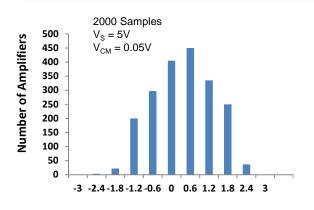
At  $T_A = +25$  °C,  $V_{CM} = V_S/2$ , and  $R_L = 10k\Omega$  connected to  $V_S/2$ , unless otherwise noted.



Quiescent Current as a function of Supply Voltage.

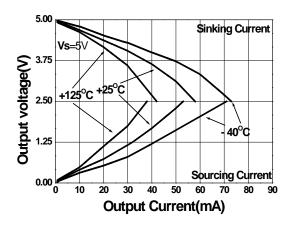


Quiescent Current as a function of Temperature.

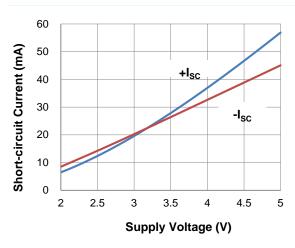


Input Offset Voltage (mV)

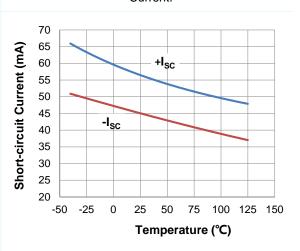
Input Offset Voltage Production Distribution.



Output Voltage Swing as a function of Output Current.



Short-circuit Current as a function of Supply Voltage.



Short-circuit Current as a function of Temperature.



### **Application Notes**

#### LOW INPUT BIAS CURRENT

The HTC852x op-amps are a CMOS op-amp family and feature very low input bias current in pA range. The low input bias current allows the amplifiers to be used in applications with high resistance sources. Care must be taken to minimize PCB Surface Leakage. See below section on "PCB Surface Leakage" for more details.

### PCB SURFACE LEAKAGE

In applications where low input bias current is critical, Printed Circuit Board (PCB) surface leakage effects need to be considered. Surface leakage is caused by humidity, dust or other contamination on the board. Under low humidity conditions, a typical resistance between nearby traces is  $10^{12}\Omega$ . A 5V difference would cause 5pA of current to flow, which is greater than the HTC852x's input bias current at +25°C ( $\pm 1 {\rm fA}$ , typical). It is recommended to use multi-layer PCB layout and route the op-amp's –IN and +IN signal under the PCB surface.

The effective way to reduce surface leakage is to use a guard ring around sensitive pins (or traces). The guard ring is biased at the same voltage as the sensitive pin. An example of this type of layout is shown in Figure 1 for Inverting Gain application.

- 1. For Non-Inverting Gain and Unity-Gain Buffer:
  - a) Connect the non-inverting pin (+IN) to the input with a wire that does not touch the PCB surface.
  - b) Connect the guard ring to the inverting input pin (– IN). This biases the guard ring to the Common Mode input voltage.
- 2. For Inverting Gain and Trans-impedance Gain Amplifiers (convert current to voltage, such as photo detectors):
  - a) Connect the guard ring to the non-inverting input pin (+IN). This biases the guard ring to the same reference voltage as the op-amp (e.g., V<sub>S</sub>/2 or ground).
  - b) Connect the inverting pin (-IN) to the input with a wire that does not touch the PCB surface.

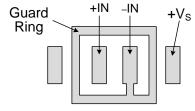


Figure 1. Use a guard ring around sensitive pins

#### GROUND SENSING AND RAIL TO RAIL

The input common-mode voltage range of the HTC852x series extends 300mV beyond the supply rails. This is achieved with a complementary input stage—an N-channel input differential pair in parallel with a P-channel differential pair. For normal operation, inputs should be limited to this range. The absolute maximum input voltage is 500mV beyond the supplies. Inputs greater than the input common-mode range but less than the maximum input voltage, while not valid, will not cause any damage to the op-amp. Unlike some other op-amps, if input current is limited, the inputs may go beyond the supplies without phase inversion, as shown in Figure 2. Since the input common-mode range extends from ( $\rm V_{S-}-0.3V)$ ) to ( $\rm V_{S+}+0.3V$ ), the HTC852x op-amps can easily perform 'true ground' sensing.

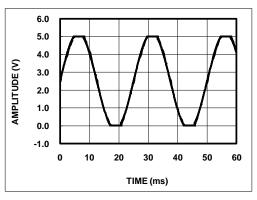


Figure 2. No Phase Inversion with Inputs Greater Than the Power-Supply Voltage

A topology of class AB output stage with common-source transistors is used to achieve rail-to-rail output. For light resistive loads (e.g.  $100k\Omega)$ , the output voltage can typically swing to within 5mV from the supply rails. With moderate resistive loads (e.g.  $10k\Omega)$ , the output can typically swing to within 10mV from the supply rails and maintain high openloop gain. See the Typical Characteristic curve, Output Voltage Swing as a function of Output Current, for more information.

The maximum output current is a function of total supply voltage. As the supply voltage to the amplifier increases, the output current capability also increases. Attention must be paid to keep the junction temperature of the IC below 150°C when the output is in continuous short-circuit. The output of the amplifier has reverse-biased ESD diodes connected to each supply. The output should not be forced more than 0.5V beyond either supply, otherwise current will flow through these diodes.

### CAPACITIVE LOAD AND STABILITY

The HTC852x can directly drive 1nF in unity-gain without oscillation. The unity-gain follower (buffer) is the most sensitive configuration to capacitive loading. Direct capacitive loading reduces the phase margin of amplifiers and this results in ringing or even oscillation. Applications that require greater capacitive drive capability should use an isolation resistor between the output and the capacitive load like the circuit in Figure 3. The isolation resistor  $R_{\rm ISO}$  and the load capacitor  $C_{\rm L}$  form a zero to increase stability. The bigger the  $R_{\rm ISO}$  resistor value, the more stable  $V_{\rm OUT}$  will be. Note that this method results in a loss of gain accuracy because  $R_{\rm ISO}$  forms a voltage divider with the  $R_{\rm L}$ .

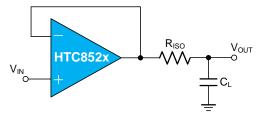


Figure 3. Indirectly Driving Heavy Capacitive Load

An improvement circuit is shown in Figure 4. It provides DC accuracy as well as AC stability. The  $R_F$  provides the DC accuracy by connecting the inverting signal with the output.



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### **Application Notes** (continued)

The  $\mathrm{C_F}$  and  $\mathrm{R_{ISO}}$  serve to counteract the loss of phase margin by feeding the high frequency component of the output signal back to the amplifier's inverting input, thereby preserving phase margin in the overall feedback loop.

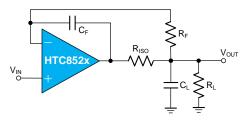


Figure 4. Indirectly Driving Heavy Capacitive Load with DC Accuracy

For no-buffer configuration, there are two others ways to increase the phase margin: (a) by increasing the amplifier's gain, or (b) by placing a capacitor in parallel with the feedback resistor to counteract the parasitic capacitance associated with inverting node.

#### POWER SUPPLY LAYOUT AND BYPASS

The HTC852x family operates from either a single +2.3V to +5.5V supply or dual  $\pm 1.15V$  to  $\pm 3.00V$  supplies. For single-supply operation, bypass the power supply  $V_S$  with a ceramic capacitor (i.e.  $0.01\mu F$  to  $0.1\mu F$ ) which should be placed close (within 2mm for good high frequency

performance) to the  $V_{\rm S}$  pin. For dual-supply operation, both the  $V_{\rm S+}$  and the  $V_{\rm S-}$  supplies should be bypassed to ground with separate 0.1µF ceramic capacitors. A bulk capacitor (i.e. 2.2µF or larger tantalum capacitor) within 100mm to provide large, slow currents and better performance. This bulk capacitor can be shared with other analog parts.

Good PC board layout techniques optimize performance by decreasing the amount of stray capacitance at the op-amp's inputs and output. To decrease stray capacitance, minimize trace lengths and widths by placing external components as close to the device as possible. Use surface-mount components whenever possible. For the op-amp, soldering the part to the board directly is strongly recommended. Try to keep the high frequency big current loop area small to minimize the EMI (electromagnetic interfacing).

#### **GROUNDING**

A ground plane layer is important for the HTC852x circuit design. The length of the current path speed currents in an inductive ground return will create an unwanted voltage noise. Broad ground plane areas will reduce the parasitic inductance.

#### INPUT-TO-OUTPUT COUPLING

To minimize capacitive coupling, the input and output signal traces should not be parallel. This helps reduce unwanted positive feedback.

### **Typical Application Circuits**

### DIFFERENTIAL AMPLIFIER

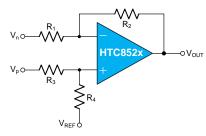


Figure 5. Differential Amplifier

The circuit shown in Figure 5 performs the difference function. If the resistors ratios are equal  $R_4/R_3 = R_2/R_1$ , then:

$$V_{OUT} = (V_p - V_n) \times R_2 / R_1 + V_{REF}$$

### INSTRUMENTATION AMPLIFIER

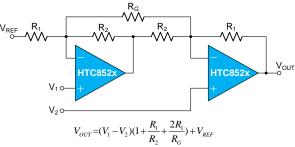
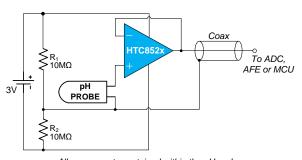


Figure 6. Instrumentation Amplifier

The HTC852x family is well suited for conditioning sensor signals in battery-powered applications. Figure 6 shows a two op-amp instrumentation amplifier, using the HTC852x op-amps. The circuit works well for applications requiring rejection of common-mode noise at higher gains. The reference voltage ( $V_{\rm REF}$ ) is supplied by a low-impedance source. In single voltage supply applications, the  $V_{\rm REF}$  is typically  $V_{\rm S}/2$ .

### **BUFFERED CHEMICAL SENSORS**



All components contained within the pH probe

Figure 7. Buffered pH Probe

The HTC852x family has input bias current in the pA range. This is ideal in buffering high impedance chemical sensors, such as pH probes. As an example, the circuit in Figure 7 eliminates expansive low-leakage cables that that is required to connect a pH probe (general purpose combination pH probes, e.g Corning 476540) to metering ICs such as ADC, AFE and/or MCU. An HTC852x op-amp



### 3.4µA, 90kHz, RRIO CMOS Operational Amplifiers

### **Typical Application Circuits** (continued)

and a lithium battery are housed in the probe assembly. A conventional low-cost coaxial cable can be used to carry the op-amp's output signal to subsequent ICs for pH reading.

#### CARBON MONOXIDE (CO) GAS SENSOR

A carbon monoxide (CO) gas detector is a device which detects the presence of carbon monoxide gas level. Usually this is battery powered and transmits audible and visible warnings. The sensor responds to CO gas by reducing its resistance proportionally to the amount of CO present in the air exposed to the internal element. On the sensor module, this variable is part of a voltage divider formed by the internal element and potentiometer  $R_{\rm 1}.$  The output of this voltage divider is fed into the non-inverting inputs of the HTC852x op-amps. The device is configured as a buffer with unity gain and is used to provide a non-loaded test point for sensor sensitivity. Because this sensor can be corrupted by parasitic electro-magnetic signals, the

HTC852x op-amps can be used for conditioning this sensor. As the Figure 8 shown, the variable resistor is used to calibrate the sensor in different environments.

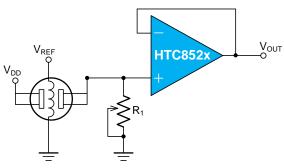


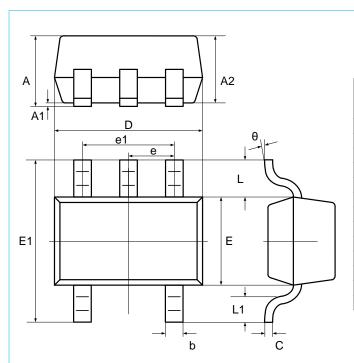
Figure 8. CO Gas Sensor Circuit.





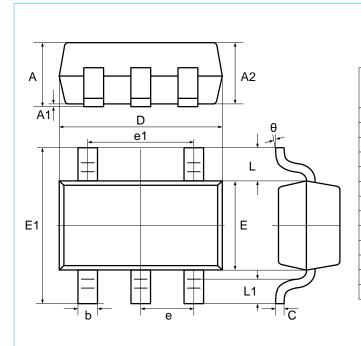
## **Package Outlines**

### SC70-5 (SOT353)



	Dimensions			sions
Symbol	In Millimeters		In In	ches
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
С	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
е	0.650	typ.	0.026	S typ.
e1	1.200	1.400	0.047	0.055
L	0.525 ref.		0.02	1 ref.
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

### SOT23-5



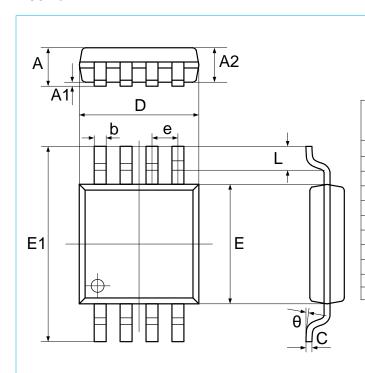
Symbol	_	nsions meters	Dimensions In Inches		
Syllibol			Min	Max	
	IVIII	Max	IVIII	IVIAX	
Α	1.040	1.350	0.042	0.055	
A1	0.040	0.150	0.002	0.006	
A2	1.000	1.200	0.041	0.049	
b	0.380	0.480	0.015	0.020	
С	0.110	0.210	0.004	0.009	
D	2.720	3.120	0.111	0.127	
Е	1.400	1.800	0.057	0.073	
E1	2.600	3.000	0.106	0.122	
е	0.950 typ.		0.037	7 typ.	
e1	1.900 typ.		0.078 typ.		
L	0.700 ref.		0.02	3 ref.	
L1	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	



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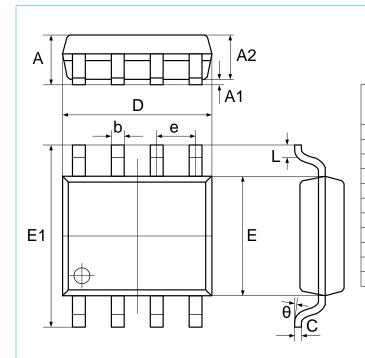
# Package Outlines (continued)

### MSOP-8



Symbol	Dimer In Milli		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.800	1.100	0.033	0.045	
A1	0.050	0.150	0.002	0.006	
A2	0.750	0.950	0.031	0.039	
b	0.290	0.380	0.012	0.016	
С	0.150	0.200	0.006	0.008	
D	2.900	3.100	0.118	0.127	
E	2.900	3.100	0.118	0.127	
E1	4.700	5.100	0.192	0.208	
е	0.650 typ.		0.026	S typ.	
L	0.400	0.700	0.016	0.029	
θ	0°	8°	0°	8°	

### **SO-8**



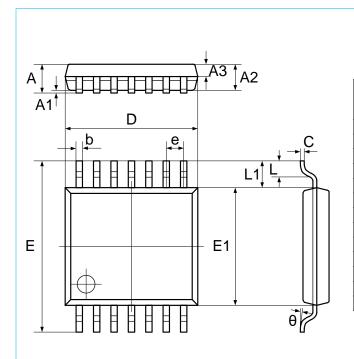
	Dimensions		Dimensions	
Symbol	In Millimeters		In Inches	
	Min	Max	Min	Max
Α	1.370	1.670	0.056	0.068
A1	0.070	0.170	0.003	0.007
A2	1.300	1.500	0.053	0.061
b	0.306	0.506	0.013	0.021
С	0.203	3 typ.	0.008 typ.	
D	4.700	5.100	0.192	0.208
Е	3.820	4.020	0.156	0.164
E1	5.800	6.200	0.237	0.253
е	1.270 typ.		0.050	typ.
L	0.450	0.750	0.018	0.306
θ	0°	8°	0°	8°





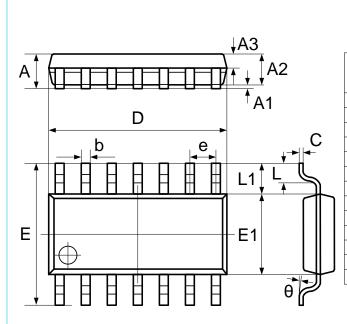
## **Package Outlines**

### TSSOP-14



Cumbal	Dimensions		Dimensions	
Symbol	In Millimeters		In Inches	
	Min	Max	Min	Max
Α	-	1.200	-	0.0472
A1	0.050	0.150	0.002	0.006
A2	0.900	1.050	0.037	0.043
А3	0.390	0.490	0.016	0.020
b	0.200	0.290	0.008	0.012
С	0.130	0.180	0.005	0.007
D	4.860	5.060	0.198	0.207
E	6.200	6.600	0.253	0.269
E1	4.300	4.500	0.176	0.184
е	0.650 typ.		0.025	6 typ.
L1	1.000 ref.		0.039	3 ref.
L	0.450	0.750	0.018	0.031
θ	0°	8°	0°	8°

### SO-14



	Dimensions		Dimensions	
Symbol	In Millimeters		In Inches	
	Min	Max	Min	Max
Α	1.450	1.850	0.059	0.076
A1	0.100	0.300	0.004	0.012
A2	1.350	1.550	0.055	0.063
А3	0.550	0.750	0.022	0.031
b	0.406	6 typ.	0.017 typ.	
С	0.203	3 typ.	0.008 typ.	
D	8.630	8.830	0.352	0.360
Е	5.840	6.240	0.238	0.255
E1	3.850	4.050	0.157	0.165
е	1.270 typ.		0.050	typ.
L1	1.040 ref.		0.04	1 ref.
L	0.350	0.750	0.014	0.031
θ	2°	8°	2°	8°



3.4µA, 90kHz, RRIO CMOS Operational Amplifiers

### **Important Notice**

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